

Seat No.: _____

Enrolment No. _____

GUJARAT TECHNOLOGICAL UNIVERSITY
BE SEM-III Examination-Dec.-2011

Subject code: 131101

Date: 20/12/2011

Subject Name: Basic Electronics

Time: 2.30 pm -5.00 pm

Total marks: 70

Instructions:

1. Attempt all questions.
2. Make suitable assumptions wherever necessary.
3. Figures to the right indicate full marks.

- Q.1** (a) Explain the concept of potential energy barrier. **07**
(b) State the limitations of Rutherford model and explain Bohr atomic model. **07**

- Q.2** (a) Explain the mobility and conductivity using electron-gas theory. Also derive the expression of current density. **07**
(b) Describe the Hall effect and also explain how it is help to determine the different properties of semiconducting material. **07**

OR

- (b) Explain the generation of holes and electrons in an intrinsic semiconductor. **07**

- Q.3** (a) Explain the formation of barrier potential in open circuited PN junction diode. Also derive the expression for barrier potential. **07**
(b) A diode having internal resistance 20Ω is used for half-wave rectification. If the applied voltage $V=50\sin(\omega t)$ and load resistance $R_L=800\Omega$, find: **07**
1) I_m , I_{dc} , I_{rms}
2) d.c. output voltage
3) efficiency of rectification.

OR

- Q.3** (a) Define the rectification and describe the full wave bridge rectifier with the help of neat circuit diagram and waveforms. **07**
(b) The resistivities of two sides of a step graded germanium diode are $2\Omega\cdot\text{cm}$ and $1\Omega\cdot\text{cm}$ for p-side and n-side respectively. Calculate the height of potential energy barrier V_o . Assume $\mu_p=1800\text{ cm}^2/\text{v}\cdot\text{sec}$, $\mu_n=2100\text{ cm}^2/\text{v}\cdot\text{sec}$, $q=1.6\times 10^{-19}$ $n_i=2.5\times 10^{13}$ per cm^3 **07**

- Q.4** (a) Define following terms: **07**
1) PIV
2) voltage equivalent of temperature
3) electric potential
4) electron volt
5) Ripple factor
6) base spreading resistance
7) pinch off voltage

- (b) Explain the different types of clipping circuits. **07**

OR

- Q.4 (a)** Explain the output characteristic of n-p-n transistor in CE configuration. Also indicate different regions. **07**
- (b)** Determine h-parameters for the two port network. Also draw the hybrid model for CE, CB and CC configurations. **07**

- Q.5 (a)** Explain DC load line and Q-point for any transistor configuration. Also state the necessity of biasing and list biasing methods for transistor. **07**
- (b)** List the basic configurations of a low frequency FET amplifier. Explain any one of them with the help of neat circuit diagram and small signal equivalent circuit. **07**

OR

- Q.5 (a)** Classify the power amplifiers based on the position of Q-point on the ac load line. Also explain Class-B push-pull amplifier. **07**
- (b)** Explain the principle of operation of JFET. Also compare FET with BJT. **07**
